

PNP Transistors

—PNP Silicon—

■■ APPLICATION: Low Frequency Amplifier and High speed switching.

■■ MAXIMUM RATINGS (Ta=25°C)

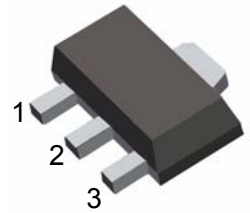
PARAMETER		SYMBOL	RATING	UNIT
Collector-base voltage		V _{CBO}	-60	V
Collector-emitter voltage		V _{CEO}	-60	V
Emitter-base voltage		V _{EBO}	-6	V
Collector current		I _c	-3	A
Base Peak current		I _{cp}	-6	A
Collector Power Dissipation	Ta=25°C	P _c	0.5	W
	Tc=25°C		2	
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	-55-150	°C

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER


■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BV _{cbo}	-60			V	I _c =-0.1mA I _e =0
Collector-Emitter Breakdown Voltage	BV _{ceo}	-60			V	I _c =-1mA I _b =0
Emitter-Base Breakdown Voltage	BV _{ebo}	-6			V	I _e =-0.1mA I _c =0
Collector Cut-off Current	I _{cbo}			-1	uA	V _{cb} =-40V I _e =0
Emitter Cut-off Current	I _{ebo}			-1	uA	V _{eb} =-4V I _c =0
Collector-Emitter Saturation Voltage	V _{ce(sat)}		-0.2	-0.5	V	I _c =-2A I _b =-0.2A
DC Current Gain	h _{FE}	120		390	β	V _{ce} =-2V I _c =-0.1A
Gain bandwidth product	f _T		180		MHz	V _{ce} =-10V I _e =10mA f=10MHz
Common Base Output Capacitance	C _{ob}		50		pF	V _{cb} =-10 V I _e =0f=1MHz
Turn on Time	t _{on}		20		ns	I _c =-3A I _e =0f=1MHz
Storage Time	t _{stg}		150		ns	I _{b1} =-300mA I _{b2} =300mA
Fall Time	t _f		20		ns	V _{cc} =-25V

■■ h_{FE} Classification And Marking

Print Mark

UNQ

Classification

Q

 h_{FE}

120~270